

AON4420L

N-Channel Enhancement Mode Field Effect Transistor

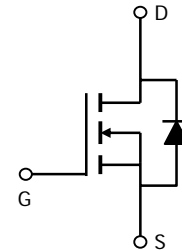
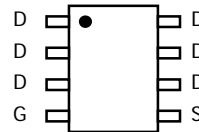
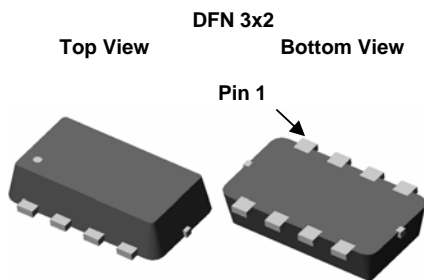
General Description

The AON4420L combines advanced trench MOSFET technology with a small footprint package to provide low $R_{DS(ON)}$ per unit area. This device is ideal for load switch and high speed switching applications.

- RoHS Compliant
- Halogen Free

Features

V_{DS} (V) = 30V
 I_D = 10A ($V_{GS} = 10V$)
 $R_{DS(ON)} < 19m\Omega$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 25m\Omega$ ($V_{GS} = 4.5V$)



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|----------------|------------------------|------------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Pulsed Drain Current ^C | I_{DM} | 50 | |
| Continuous Drain Current ^A | I_D | $T_A=25^\circ\text{C}$ | 10 |
| | | $T_A=70^\circ\text{C}$ | 8 |
| Power Dissipation ^A | P_D | $T_A=25^\circ\text{C}$ | 1.6 |
| | | $T_A=70^\circ\text{C}$ | 1 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|--------------|-----|--------------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | $t \leq 10s$ | 34 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Ambient ^A | | Steady-State | 66 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Lead ^B | $R_{\theta JL}$ | 20 | 25 | $^\circ\text{C/W}$ |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|---|-----|----------|--------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D = 250μA, V _{GS} = 0V | 30 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 30V, V _{GS} = 0V T _J = 55°C | | | 1 5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} = 0V, V _{GS} = ±20V | | | ±100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 1.4 | 1.9 | 2.5 | V |
| I _{D(ON)} | On state drain current | V _{GS} = 10V, V _{DS} = 5V | 50 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} = 10V, I _D = 10A T _J = 125°C | | 16 27 | 20 | mΩ |
| | | V _{GS} = 4.5V, I _D = 8A | | 21 | 26 | |
| g _{FS} | Forward Transconductance | V _{DS} = 5V, I _D = 10A | | 30 | | S |
| V _{SD} | Diode Forward Voltage | I _S = 1A, V _{GS} = 0V | | 0.75 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 3 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} = 0V, V _{DS} = 15V, f = 1MHz | 440 | 550 | 660 | pF |
| C _{oss} | Output Capacitance | | 80 | 110 | 140 | pF |
| C _{rss} | Reverse Transfer Capacitance | | 35 | 55 | 80 | pF |
| R _g | Gate resistance | V _{GS} = 0V, V _{DS} = 0V, f = 1MHz | 2 | 4 | 6 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _g (10V) | Total Gate Charge (10V) | V _{GS} = 10V, V _{DS} = 15V, I _D = 10A | 8 | 9.8 | 12 | nC |
| Q _g (4.5V) | Total Gate Charge (4.5V) | | 4 | 4.6 | 5.5 | nC |
| Q _{gs} | Gate Source Charge | | 1.5 | 1.8 | 2.2 | nC |
| Q _{gd} | Gate Drain Charge | | 1.3 | 2.2 | 3 | nC |
| t _{D(on)} | Turn-On Delay Time | V _{GS} = 10V, V _{DS} = 15V, R _L = 1.5Ω, R _{GEN} = 3Ω | | 5 | | ns |
| t _r | Turn-On Rise Time | | | 3.2 | | ns |
| t _{D(off)} | Turn-Off Delay Time | | | 24 | | ns |
| t _f | Turn-Off Fall Time | | | 6 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F = 10A, dI/dt = 300A/μs | 8 | 11 | 14 | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F = 10A, dI/dt = 300A/μs | 11 | 13 | 16 | nC |

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using t ≤ 300μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s thermal resistance rating.

Rev0: July 2008

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

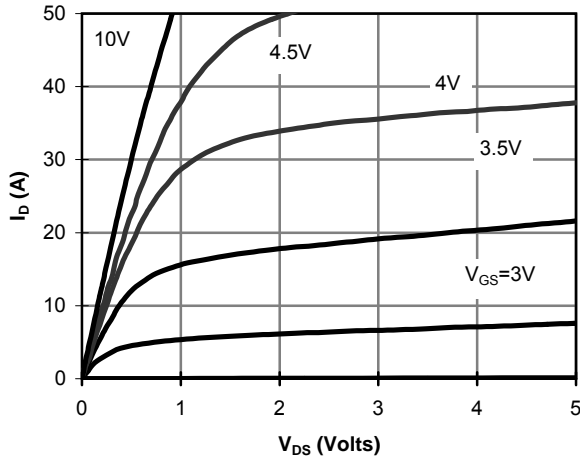


Figure 1: On-Region Characteristics

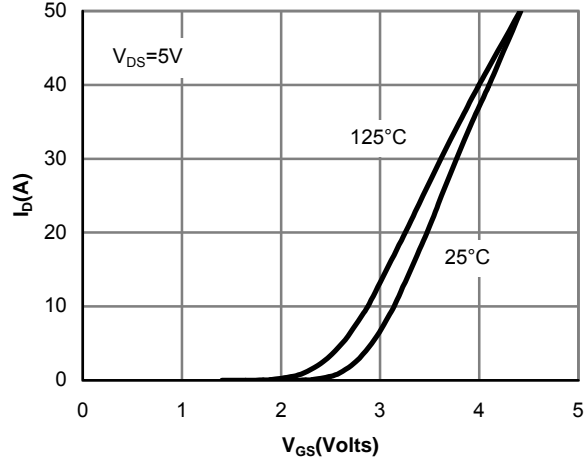


Figure 2: Transfer Characteristics

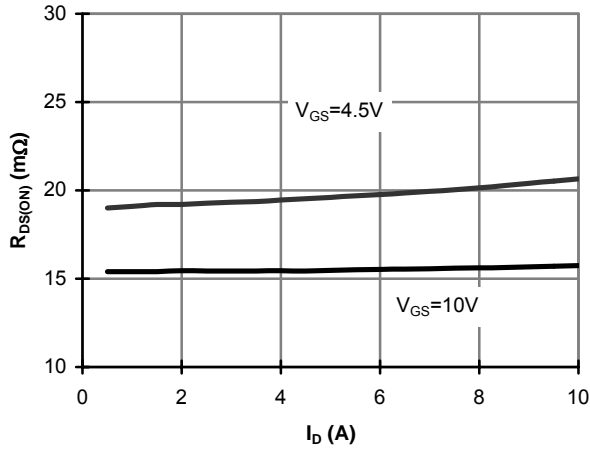


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

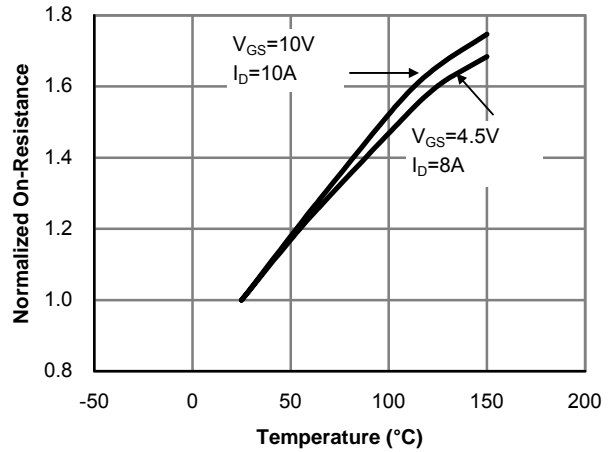


Figure 4: On-Resistance vs. Junction Temperature

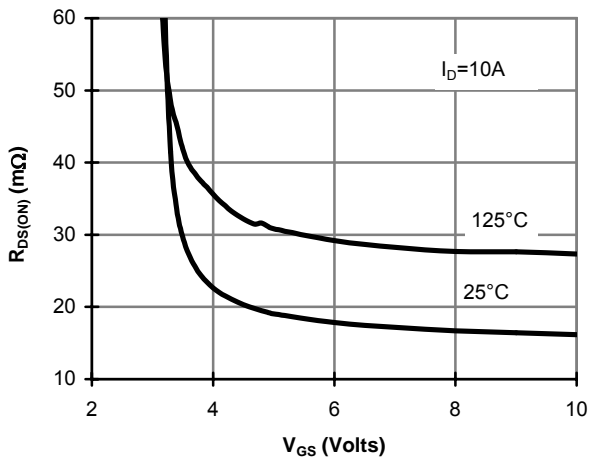


Figure 5: On-Resistance vs. Gate-Source Voltage

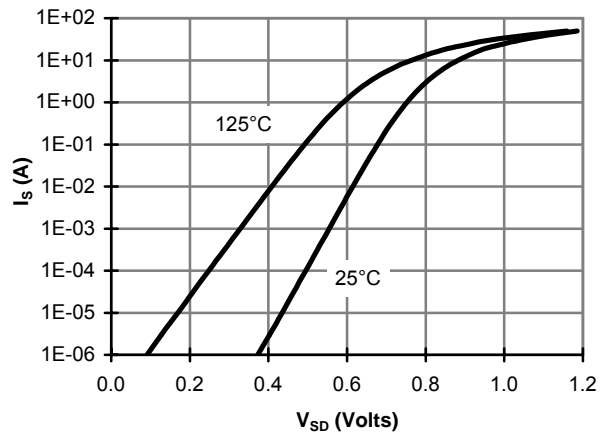


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

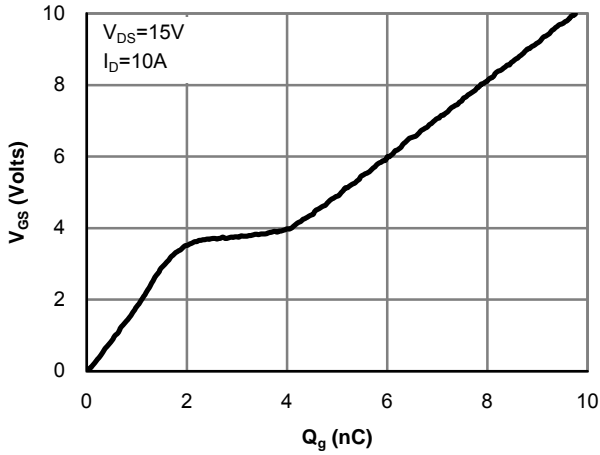


Figure 7: Gate-Charge Characteristics

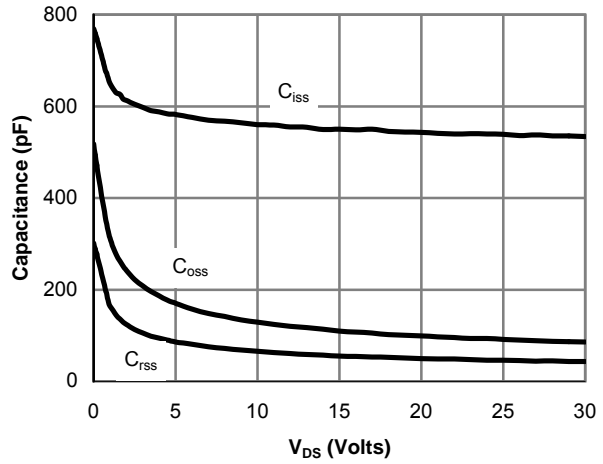


Figure 8: Capacitance Characteristics

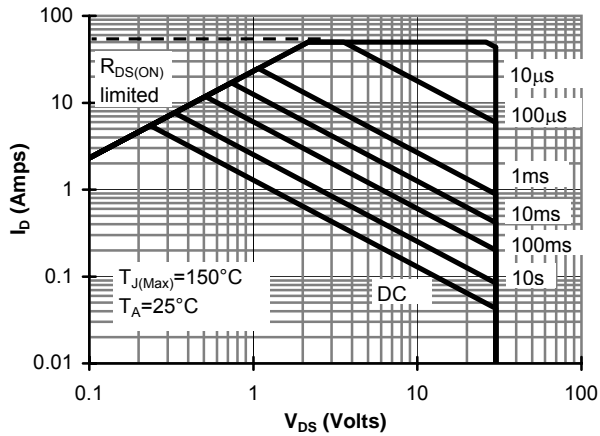


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

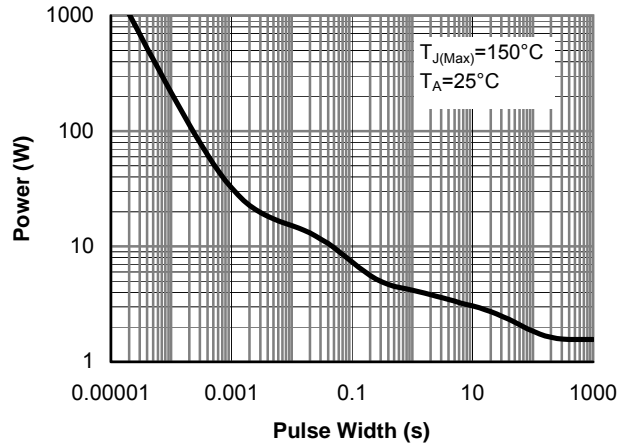


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

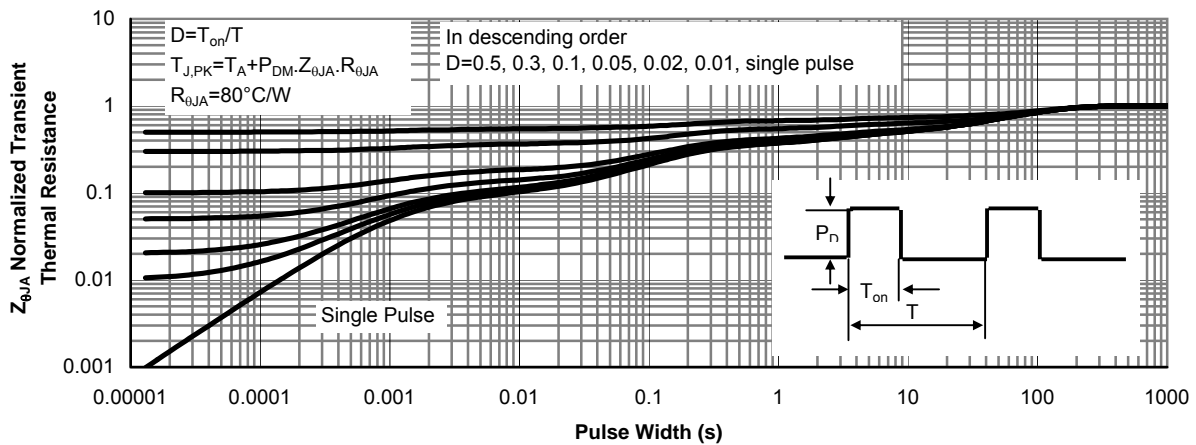
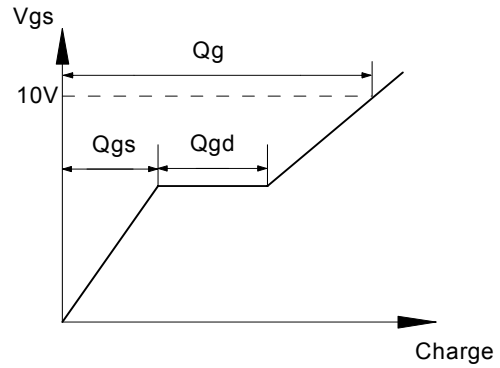
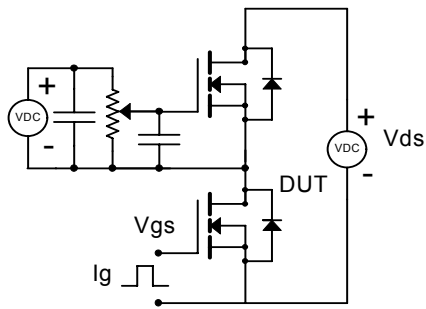
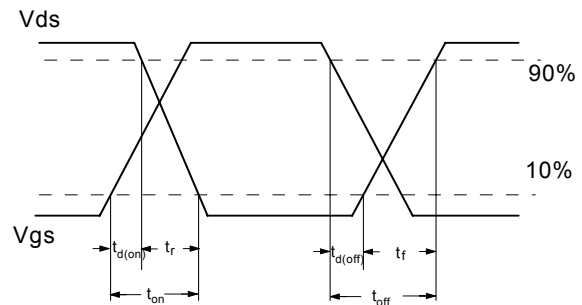
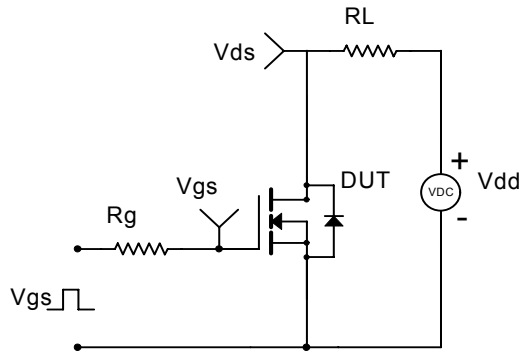


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

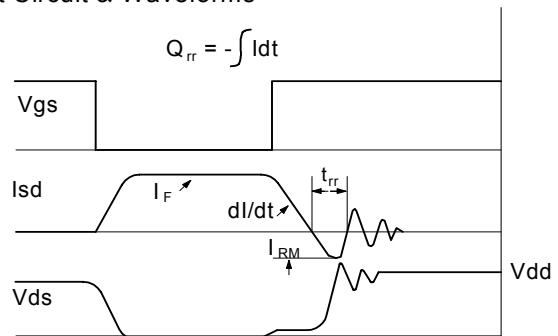
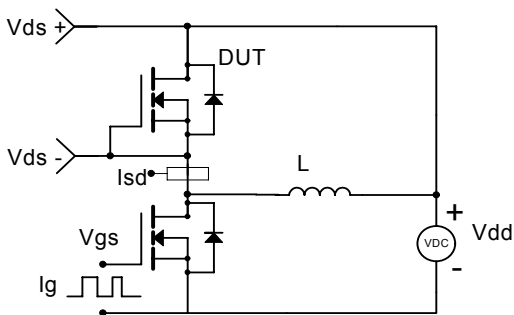
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



单击下面可查看定价，库存，交付和生命周期等信息

[>>AOS\(万代\)](#)